

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	294	(438/399).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:45
L3	447	(438/201).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:46
L4	89	(438/206).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:47
L5	684	(438/241).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:47
L7	271	(438/262).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:48
L8	494	(438/266).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:48
L10	420	(438/279).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:48
L13	644	((fin adj field adj effect\$3 adj transistor) or ("finfet")) and semiconductor)"clm."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:53

L14	298	((((fin adj field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor).clm."	US-PGPUB	OR	ON	2006/01/06 14:09
L15	76	((((fin adj field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor).clm.	US-PGPUB	OR	ON	2006/01/06 13:53
L16	10	((((fin adj field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor and gate and trench and source and drain).clm.	US-PGPUB	OR	ON	2006/01/06 14:10
L17	1010	(438/275).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:55
L18	15	((((field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor and gate and trench and source and drain and fin).clm.	US-PGPUB	OR	ON	2006/01/06 14:11
L19	201	((((field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor and gate and trench and source and drain and fin)	US-PGPUB	OR	ON	2006/01/06 14:12
L20	257	((((field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor and gate and trench and source and drain and fin) and @ad<="20030130"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 14:15
L21	202	((((field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor and gate and trench and source and drain and fin) and (single or mono) and @ad<="20030130"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 14:16
L22	50	((((field adj effect\$3 adj transistor) or ("finfet"))) and semiconductor and gate and trench and source and drain and fin) and ((single adj crystalline) or (monocrystalline or (mono adj crystalline))) and @ad<="20030130"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 14:18
L23	910	(438/199).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 14:18

L24	853	(438/258).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 14:21
S1	608	((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact	US-PGPUB; USPAT	OR	ON	2005/09/23 08:52
S3	399	((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact and @ad<="20030130"	US-PGPUB; USPAT	OR	ON	2005/09/23 08:53
S4	388	((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact and @ad<="20030130" and semiconductor	US-PGPUB; USPAT	OR	ON	2005/09/23 08:54
S5	1319	(438/197).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 13:44
S6	7	438/197.ccls. and ((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact and @ad<="20030130" and semiconductor	US-PGPUB; USPAT	OR	ON	2005/09/23 08:55
S7	7	438/197.ccls. and ((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact and @ad<="20030130" and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:51
S8	210	"438"/\$.ccls. and ((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact and @ad<="20030130" and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:57
S9	332	"257"/\$.ccls. and ((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact and @ad<="20030130" and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:55

S10	8	((("6413802") or ("20040062501") or ("4,844,604") or ("5,881,194") or ("5,908,873") or ("6,187,835") or ("6,197,422") or ("6,130,980"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/09/23 10:02
S11	332	"257"/\$.cccls. and ((vertical adj transistor adj structure) or ("FIN")) and (lithograp\$4) and gate and contact and @ad<="20030130" and semiconductor	US-PGPUB; USPAT	OR	ON	2005/09/23 09:55
S12	62	"438"/\$.cccls. and ((fin adj field adj effect\$3 adj transistor) or ("finfet")) and @ad<="20030130" and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:59
S13	105	"257"/\$.cccls. and ((fin adj field adj effect\$3 adj transistor) or ("finfet")) and @ad<="20030130" and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 13:53
S14	1	("20050014318").PN.	US-PGPUB; USPAT	OR	OFF	2005/09/23 10:02